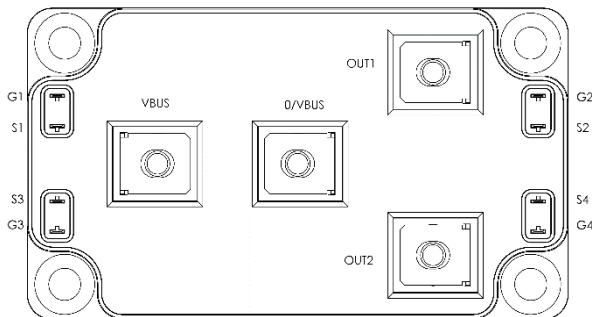
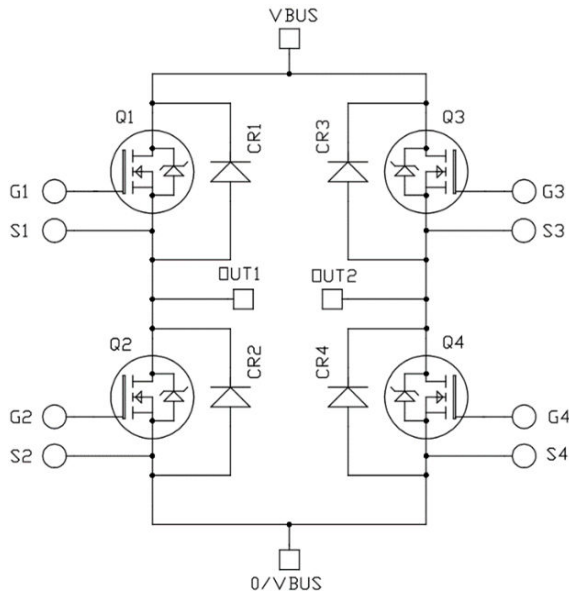


Full Bridge SiC Power Module

Product Overview

The MSCSM120HM063CAG device is a 1200 V, 333 A full bridge silicon carbide (SiC) power module.



All ratings at $T_j = 25\text{ }^\circ\text{C}$, unless otherwise specified.

Caution: These devices are sensitive to electrostatic discharge. Proper handling procedures must be followed.

Features

The following are key features of the MSCSM120HM063CAG device:

- SiC Schottky Diode
 - Zero reverse recovery
 - Zero forward recovery
 - Temperature independent switching behavior
 - Positive temperature coefficient on VF
- SiC Power MOSFET
 - Low $R_{DS(on)}$
 - High temperature performance
- Kelvin source for easy drive
- Low stray inductance
- M5 power connectors
- Aluminum nitride (AlN) substrate for improved thermal performance

Benefits

The following are benefits of the MSCSM120HM063CAG device:

- High efficiency converter
- Outstanding performance at high frequency operation
- Stable temperature behavior
- Direct mounting to heatsink (isolated package)
- Low junction-to-case thermal resistance
- RoHS compliant

Application

The MSCSM120HM063CAG device is designed for the following applications:

- Welding converters
- Switched mode power supplies
- Uninterruptible power supplies
- EV motor and traction drive

1. Electrical Specifications

This section provides the electrical specifications of the MSCSM120HM063CAG device.

1.1 SiC MOSFET Characteristics

The following table lists the absolute maximum ratings per SiC MOSFET of the MSCSM120HM063CAG device.

Table 1-1. Absolute Maximum Ratings per SiC MOSFET

Symbol	Parameter	Maximum Ratings	Unit
V_{DSS}	Drain-Source voltage	1200	V
I_D	Continuous drain current	$T_C = 25\text{ }^\circ\text{C}$	333
		$T_C = 80\text{ }^\circ\text{C}$	265
I_{DM}	Pulsed drain current	660	
V_{GS}	Gate-Source voltage	-10/25	V
$R_{DS(on)}$	Drain-Source ON resistance	7.8	m Ω
P_D	Power dissipation	$T_C = 25\text{ }^\circ\text{C}$	873

Note: 1. Specification of SiC MOSFET device but output current must be limited due to size of power connectors.

The following table lists the electrical characteristics per SiC MOSFET of the MSCSM120HM063CAG device.

Table 1-2. Electrical Characteristics per SiC MOSFET

Symbol	Characteristics	Test Conditions	Min	Typ	Max	Unit	
I_{DSS}	Zero gate voltage drain current	$V_{GS} = 0\text{ V}; V_{DS} = 1200\text{ V}$	—	40	400	μA	
$R_{DS(on)}$	Drain-Source on resistance	$V_{GS} = 20\text{ V}$ $I_D = 80\text{ A}$	$T_J = 25\text{ }^\circ\text{C}$	—	6.3	7.8	m Ω
			$T_J = 175\text{ }^\circ\text{C}$	—	10	—	
$V_{GS(th)}$	Gate threshold voltage	$V_{GS} = V_{DS}, I_D = 4\text{ mA}$	1.8	2.8	—	V	
I_{GSS}	Gate-Source leakage current	$V_{GS} = 20\text{ V}, V_{DS} = 0\text{ V}$	—	—	400	nA	

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Electrical Specifications

The following table lists the dynamic characteristics per SiC MOSFET of the MSCSM120HM063CAG device.

Table 1-3. Dynamic Characteristics per SiC MOSFET

Symbol	Characteristics	Test Conditions	Min	Typ	Max	Unit
C_{iss}	Input capacitance	$V_{GS} = 0\text{ V}$	—	12	—	nF
C_{oss}	Output capacitance	$V_{DS} = 1000\text{ V}$	—	1	—	
C_{riss}	Reverse transfer capacitance	$f = 1\text{ MHz}$	—	0.1	—	
Q_g	Total gate charge	$V_{GS} = -5\text{ V}/20\text{ V}$	—	928	—	nC
Q_{gs}	Gate–Source charge	$V_{Bus} = 800\text{ V}$	—	164	—	
Q_{gd}	Gate–Drain charge	$I_D = 160\text{ A}$	—	200	—	
$T_{d(on)}$	Turn-on delay time	$V_{GS} = -5\text{ V}/20\text{ V}$	—	60	—	ns
T_r	Rise time	$V_{Bus} = 600\text{ V}$	—	50	—	
$T_{d(off)}$	Turn-off delay time	$I_D = 200\text{ A}; T_J = 150\text{ °C}$	—	180	—	
T_f	Fall time	$R_{G(ON)} = 2\ \Omega; R_{G(OFF)} = 1.2\ \Omega$	—	30	—	
E_{on}	Turn-on energy	$V_{GS} = -5/20\text{ V}$	—	4.1	—	mJ
E_{off}	Turn-off energy	$V_{Bus} = 600\text{ V}$ $I_D = 200\text{ A}$ $R_{G(ON)} = 2\ \Omega$ $R_{G(OFF)} = 1.2\ \Omega$				
R_{Gint}	Internal gate resistance		—	1.5	—	Ω
R_{thJC}	Junction-to-case thermal resistance		—	—	0.11	$^{\circ}\text{C}/\text{W}$

The following table lists the body diode ratings and characteristics per SiC MOSFET of the MSCSM120HM063CAG device.

Table 1-4. Body Diode Ratings and Characteristics per SiC MOSFET

Symbol	Characteristics	Test Conditions	Min	Typ	Max	Unit
V_{SD}	Diode forward voltage	$V_{GS} = 0\text{ V}; I_{SD} = 160\text{ A}$	—	4	—	V
		$V_{GS} = -5\text{ V}; I_{SD} = 160\text{ A}$	—	4.2	—	
t_{rr}	Reverse recovery time	$I_{SD} = 160\text{ A}$ $V_{GS} = -5\text{ V}$	—	90	—	ns
Q_{rr}	Reverse recovery charge	$V_R = 800\text{ V}$ $di_F/dt = 4000\text{ A}/\mu\text{s}$	—	2200	—	nC
I_{rr}	Reverse recovery current		—	54	—	A

1.2 SiC Schottky Diode Ratings and Characteristics

The following table lists the SiC diode ratings and characteristics per SiC diode of MSCSM120HM063CAG device.

Table 1-5. SiC Schottky Diode Ratings and Characteristics

Symbol	Characteristics	Test Conditions		Min	Typ	Max	Unit
V_{RRM}	Peak repetitive reverse voltage			—	—	1200	V
I_{RRM}	Reverse leakage current	$V_R = 1200\text{ V}$	$T_J = 25\text{ °C}$	—	40	800	μA
			$T_J = 175\text{ °C}$	—	600	—	
I_F	DC forward current	—	$T_C = 100\text{ °C}$	—	120	—	A
V_F	Diode forward voltage	$I_F = 120\text{ A}$	$T_J = 25\text{ °C}$	—	1.5	1.8	V
			$T_J = 175\text{ °C}$	—	2.1	—	
Q_C	Total capacitive charge	$V_R = 600\text{ V}$	—	—	520	—	nC
C	Total capacitance	$f = 1\text{ MHz}, V_R = 400\text{ V}$		—	564	—	pF
		$f = 1\text{ MHz}, V_R = 800\text{ V}$		—	420	—	
R_{thJC}	Junction-to-case thermal resistance			—	—	0.26	$^{\circ}\text{C/W}$

1.3 Thermal and Package Characteristics

The following table lists the thermal and package characteristics of MSCSM120HM063CAG device.

Table 1-6. Thermal and Package Characteristics

Symbol	Characteristics		Min	Max	Unit
V_{ISOL}	RMS isolation voltage, any terminal to case $t = 1\text{ min}, 50\text{ Hz}/60\text{ Hz}$		4000	—	V
T_J	Operating junction temperature range		−40	175	$^{\circ}\text{C}$
T_{JOP}	Recommended junction temperature under switching conditions		−40	$T_{Jmax} - 25$	
T_{STG}	Storage temperature range		−40	125	
T_C	Operating case temperature		−40	125	
Torque	Mounting torque	To heatsink M6	3	5	N.m
		For terminals M5	2	3.5	
Wt	Package weight		—	300	g

1.4 Typical SiC MOSFET Performance Curve

This section shows the typical SiC MOSFET performance curves of the MSCSM120HM063CAG device.

Figure 1-1. Maximum Thermal Impedance

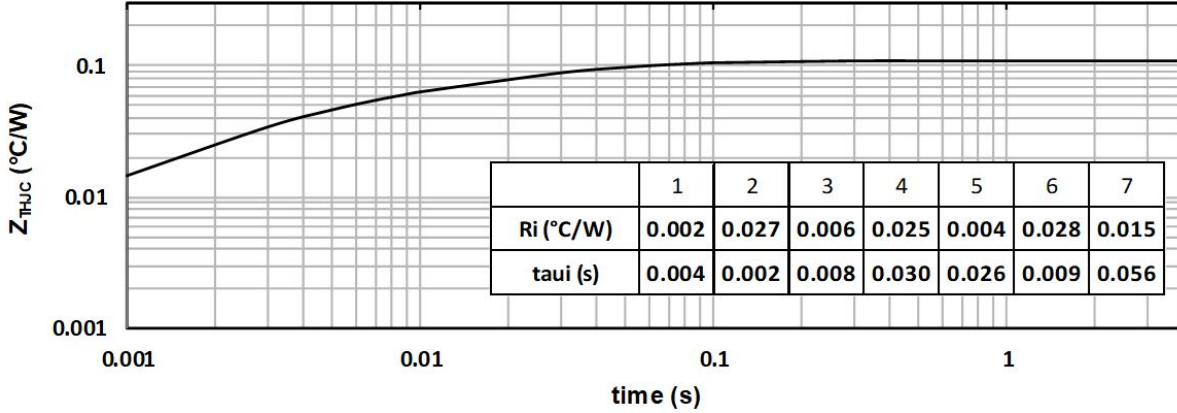


Figure 1-2. Output Characteristics, $T_J = 25^{\circ}C$

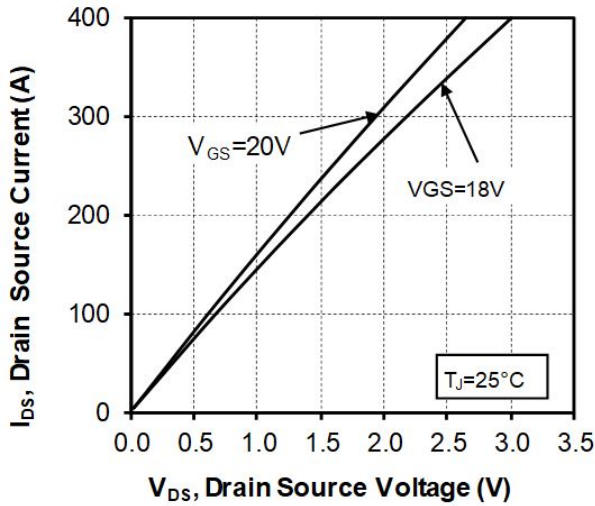


Figure 1-3. Output Characteristics, $T_J = 175^{\circ}C$

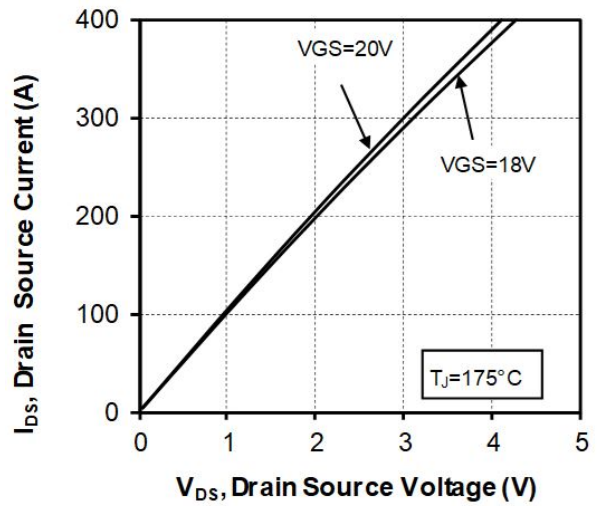


Figure 1-4. Normalized $R_{DS(on)}$ vs. Temperature

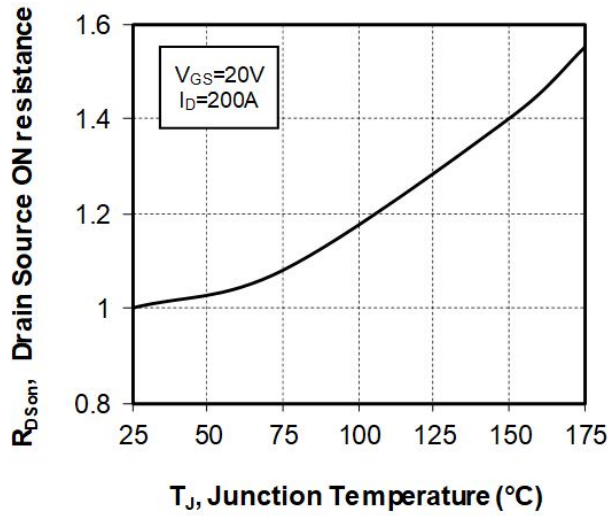


Figure 1-5. Transfer Characteristics

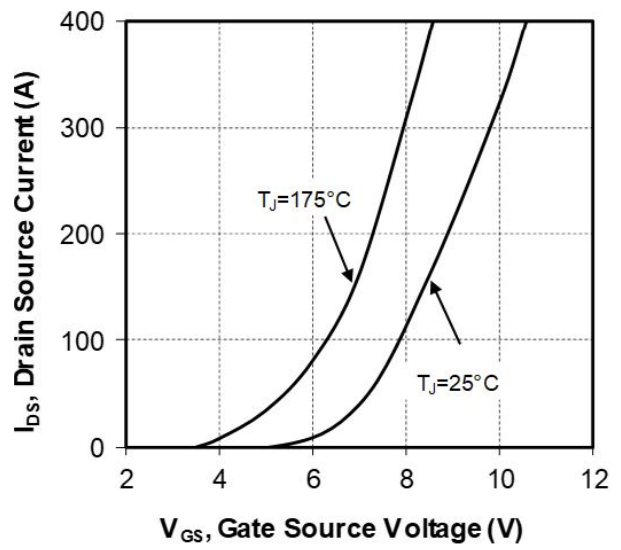


Figure 1-6. Switching Energy vs R_g

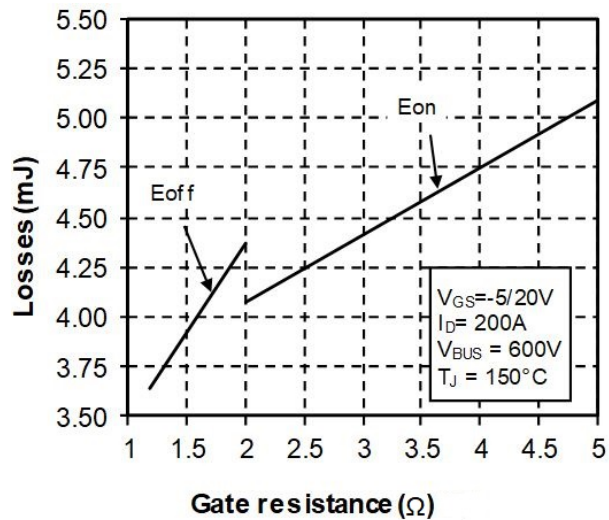
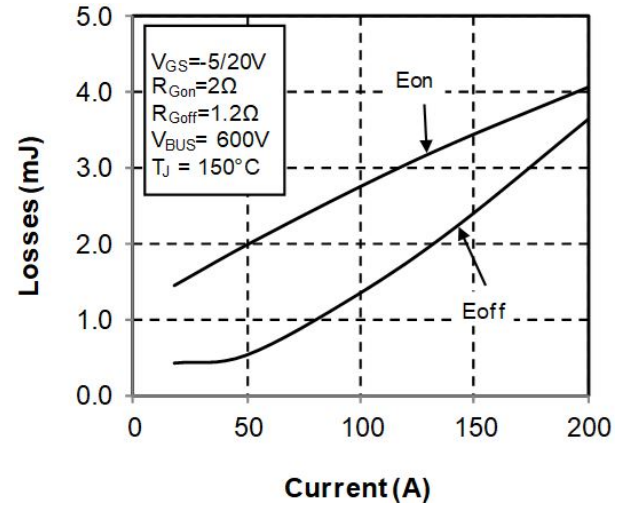


Figure 1-7. Switching Energy vs Current



MSCSM120HM063CAG

Electrical Specifications

Figure 1-8. Capacitance vs. Drain Source Voltage

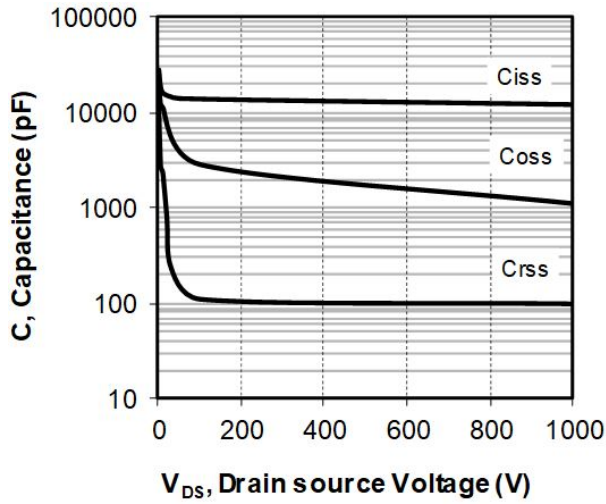


Figure 1-9. Gate Charge vs. Gate Source Voltage

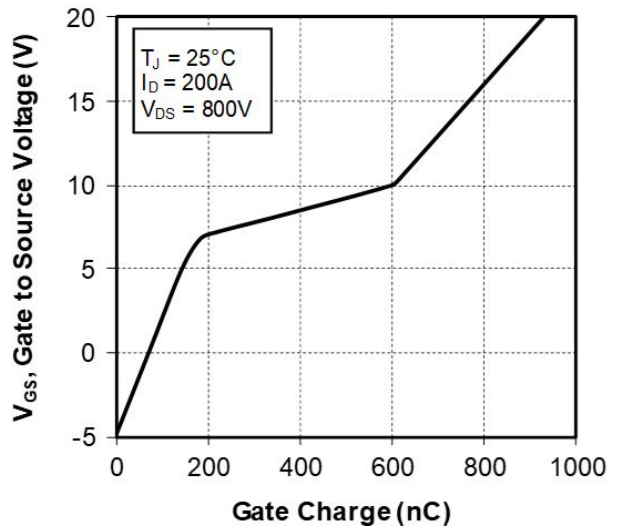


Figure 1-10. Body Diode Characteristics, $T_J = 25^\circ\text{C}$

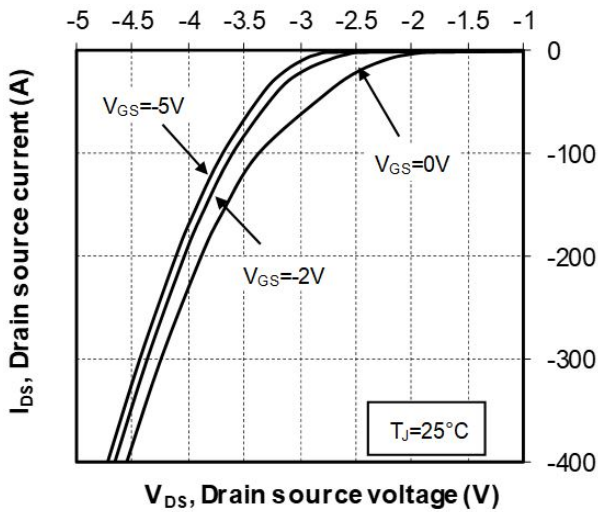


Figure 1-11. 3rd Quadrant Characteristics, $T_J = 25^\circ\text{C}$

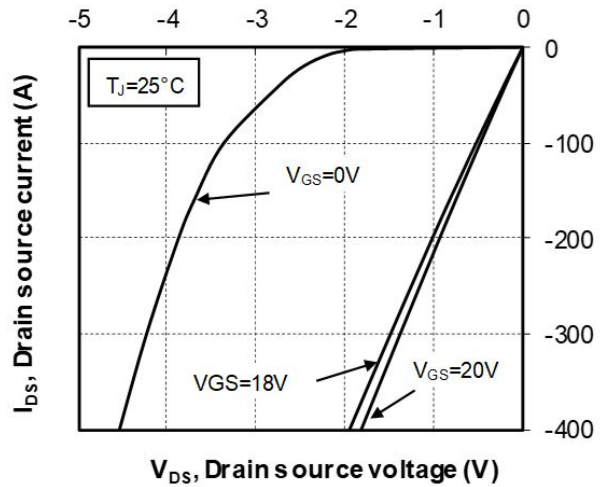


Figure 1-12. Body Diode Characteristics, $T_J = 175^\circ\text{C}$

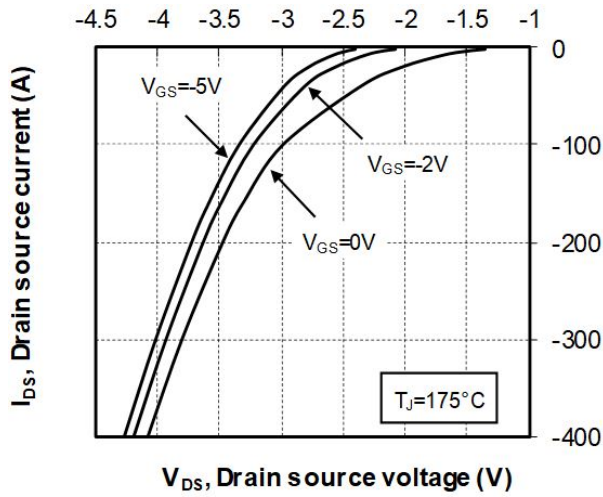


Figure 1-13. 3rd Quadrant Characteristics, $T_J = 175^\circ\text{C}$

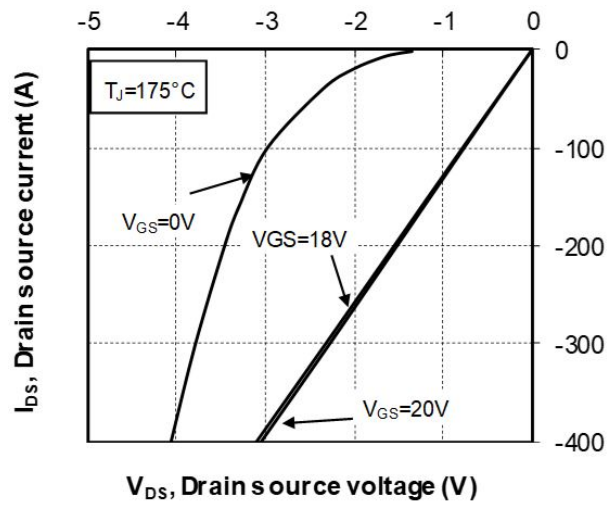
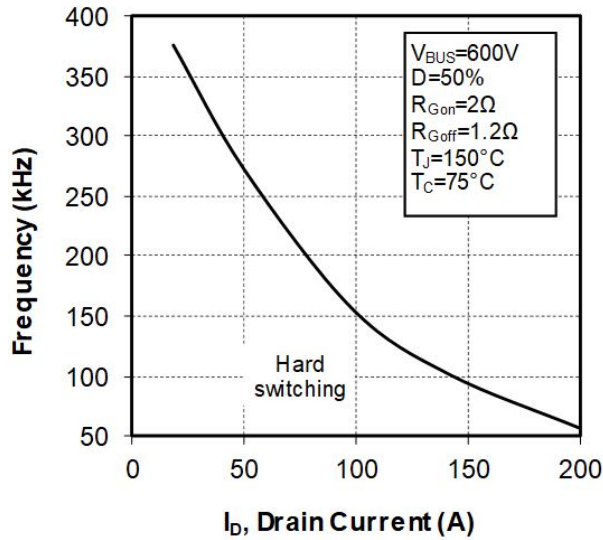


Figure 1-14. Operating Frequency vs. Drain Current



1.5 Typical SiC Diode Performance Curve

This section shows the typical SiC diode performance curves of MSCSM120HM063CAG device.

Figure 1-15. Maximum Thermal Impedance

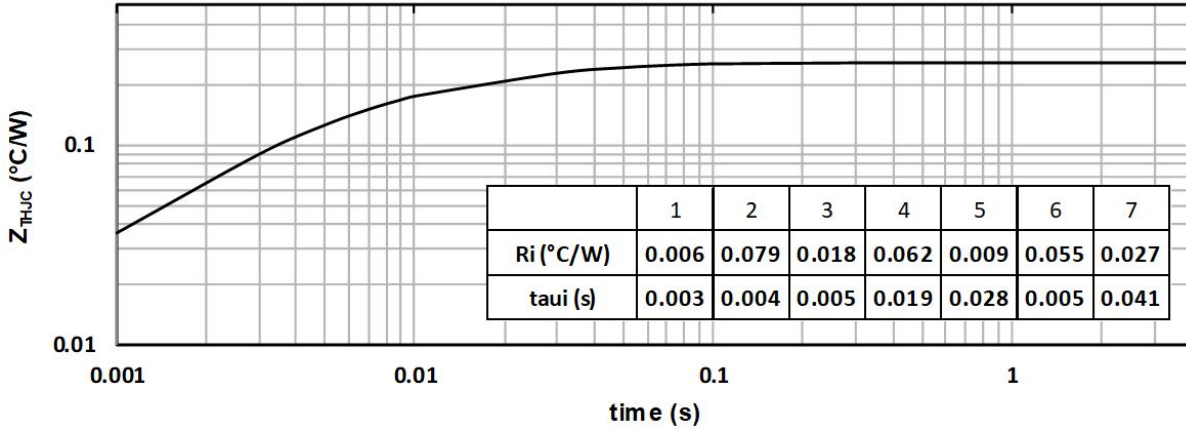


Figure 1-16. Forward Characteristics

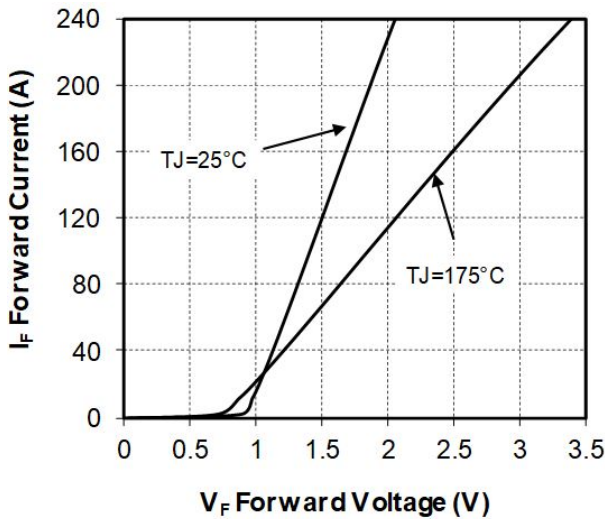
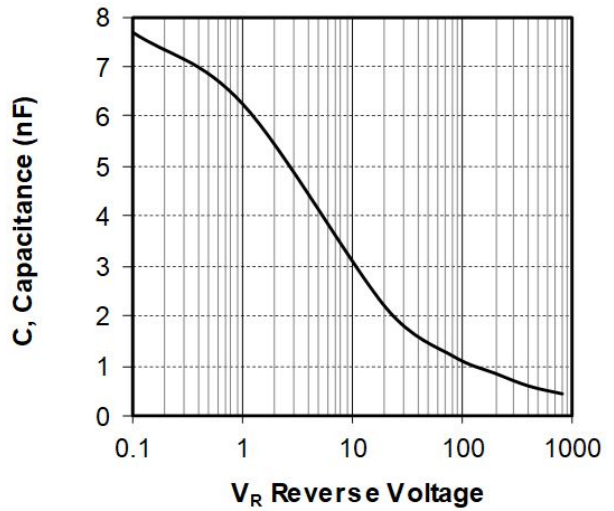


Figure 1-17. Capacitance vs. Reverse Voltage



MSCSM120HM063CAG

Package Specifications

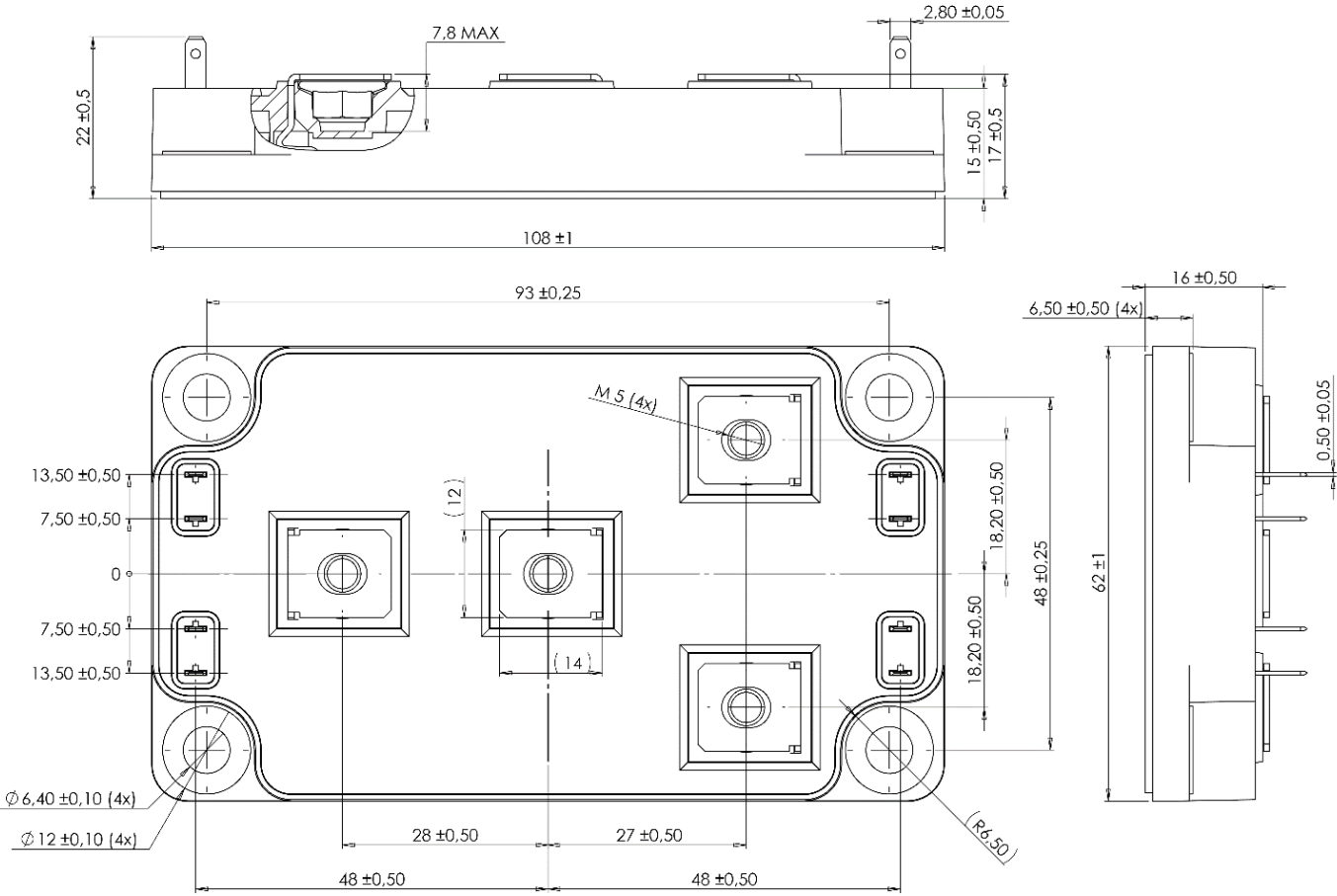
2. Package Specifications

The following section shows the package specification of MSCSM120HM063CAG device.

2.1 Package Outline

The following figure shows the package outline drawing of MSCSM120HM063CAG device. The dimensions are in millimeters.

Figure 2-1. Package Outline Drawing



Note: See [Application Note APT0601—Mounting instructions for SP6 Power Modules](#) for more information.

3. Revision History

Revision	Date	Description
A	04/2021	This is the first publication of this document.

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